

2PYP LWP N T T Y

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS[®] Generic series is optimized for extreme switching performance to minimize switching loss. It is tailored for high power density applications to meet the highest efficiency standards.

1PL P

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity




, VNL T Y

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

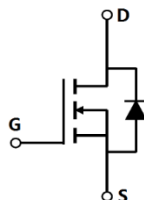
6P P XLYNP L LXPP

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	700	V
$I_{D, pulse}$	45	A
$R_{DS(ON), max} @ V_{GS}=10V$	290	m
Q_g	18	nC

8 L VTYR 4Y XL T Y

Product Name	Package	Marking
OSG65R290AF	TO251	OSG65R290A

LNMLRP TY 4Y XL T Y



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	15	A
Continuous drain current ¹⁾ , $T_C=100^{\circ}\text{C}$		9.3	
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, pulse}$	45	A
Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_S	15	A
Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{S, pulse}$	45	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	104	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	400	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 480\text{ V}$, $I_{SD} = I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	R_{JC}	1.2	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	R_{JA}	62.5	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	650			V	$V_{GS}=0\text{ V}$, $I_D=250\ \mu\text{A}$
		700	740			$V_{GS}=0\text{ V}$, $I_D=250\ \mu\text{A}$, $T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$V_{DS}=V_{GS}$, $I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.26	0.29		$V_{GS}=10\text{ V}$, $I_D=7.5\text{ A}$
			0.68			$V_{GS}=10\text{ V}$, $I_D=7.5\text{ A}$, $T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=650\text{ V}$, $V_{GS}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		986		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}		67.7		pF	
Reverse transfer capacitance	C_{rss}		3.36		pF	
Turn-on delay time	$t_{d(on)}$		30.9		ns	$V_{GS}=10\text{ V}$, $V_{DS}=520\text{ V}$, $R_G=25\ \Omega$, $I_D=15\text{ A}$
Rise time	t_r		39.9		ns	
Turn-off delay time	$t_{d(off)}$		44.1		ns	
Fall time	t_f		49.7		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		18		nC	$V_{GS}=10\text{ V}$, $V_{DS}=520\text{ V}$, $I_D=15\text{ A}$
Gate-source charge	Q_{gs}		5.9		nC	
Gate-drain charge	Q_{gd}		6		nC	
Gate plateau voltage	$V_{plateau}$		5.6		V	

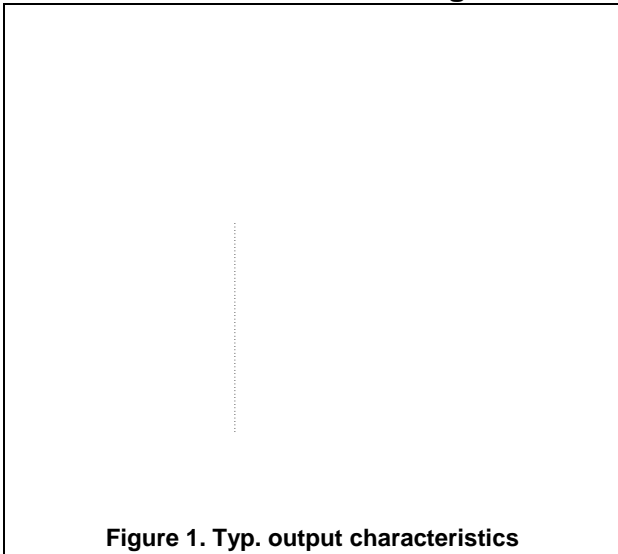
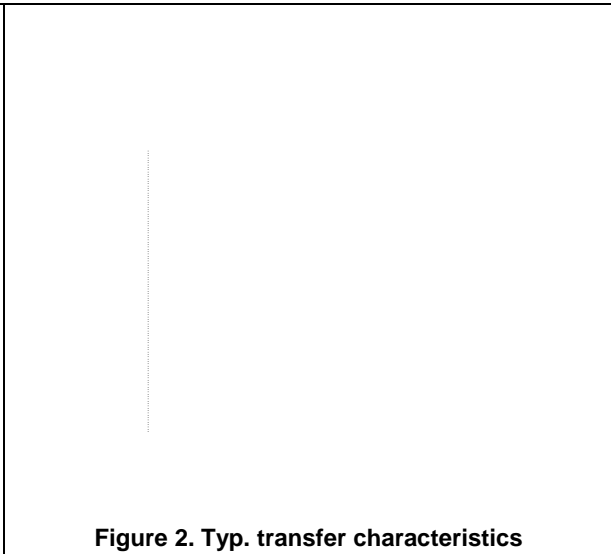
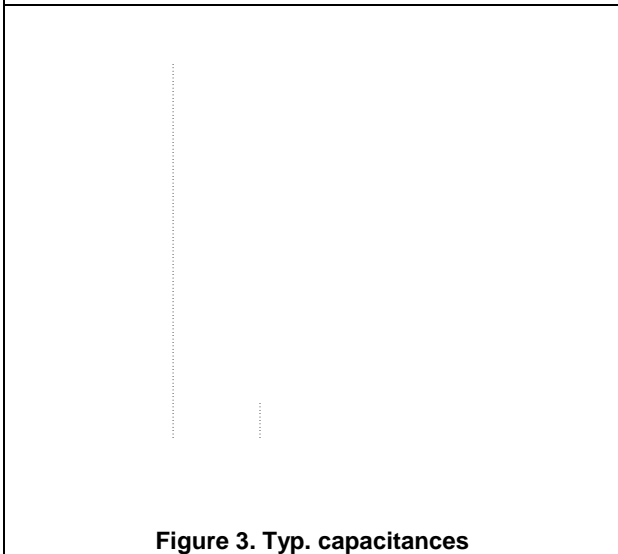
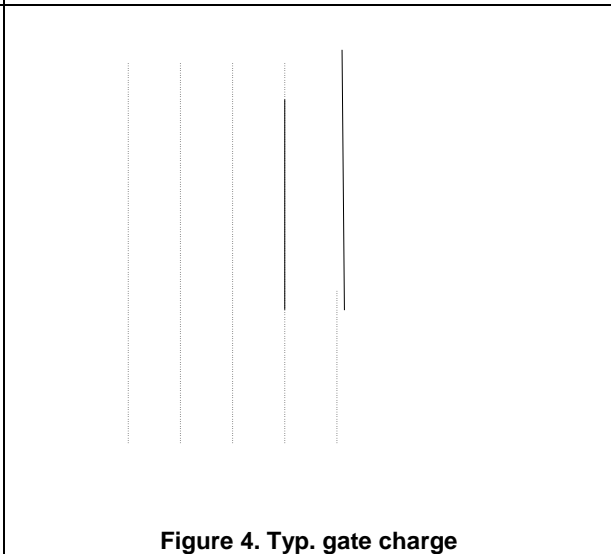
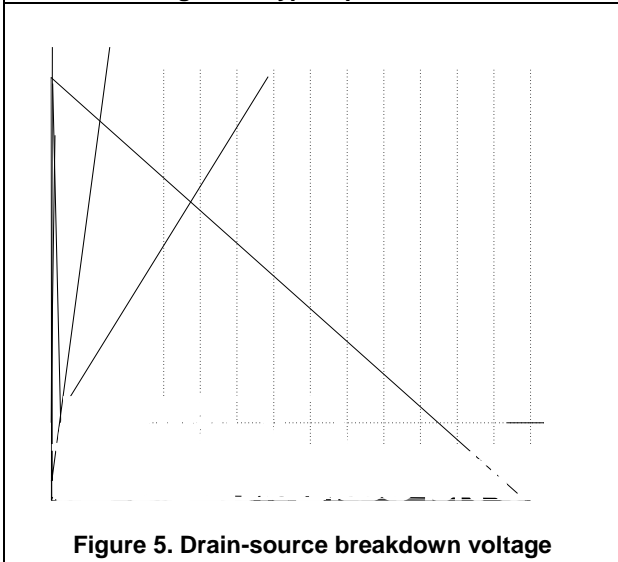
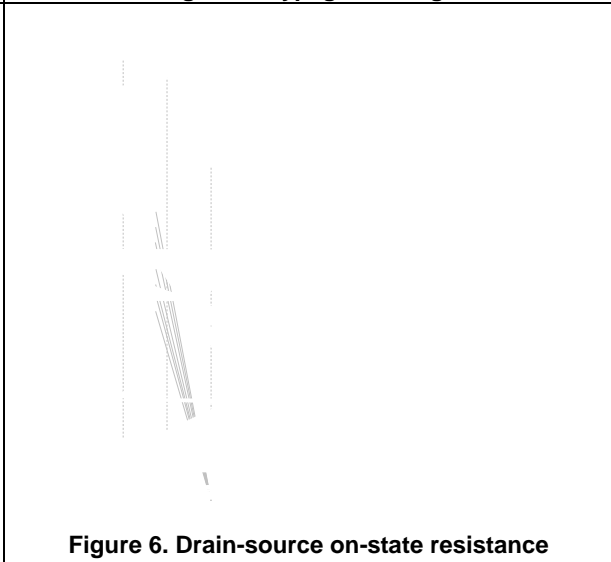
Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.4	V	$I_S=15\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		352.9		ns	$I_S=15\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		4.4		μC	
Peak reverse recovery current	I_{rrm}		23.1		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of R_{JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=20\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams

 <p>Figure 1. Typ. output characteristics</p>	 <p>Figure 2. Typ. transfer characteristics</p>
 <p>Figure 3. Typ. capacitances</p>	 <p>Figure 4. Typ. gate charge</p>
 <p>Figure 5. Drain-source breakdown voltage</p>	 <p>Figure 6. Drain-source on-state resistance</p>

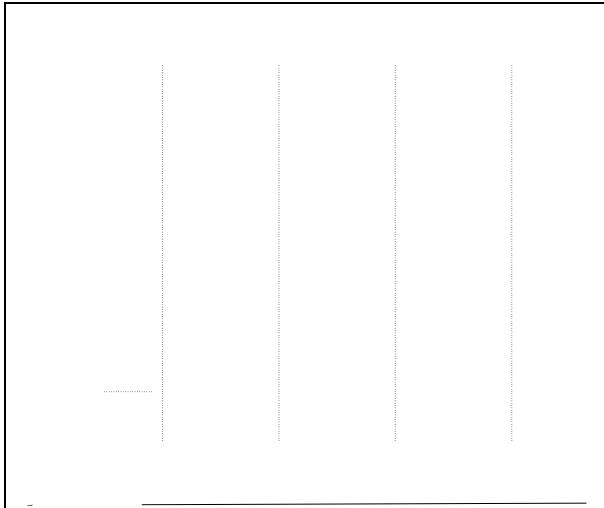


Figure 7. Forward characteristic of body diode

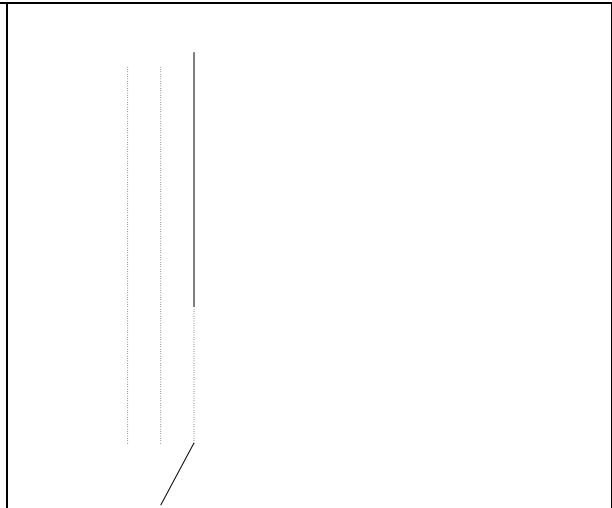


Figure 8. Drain-source on-state resistance

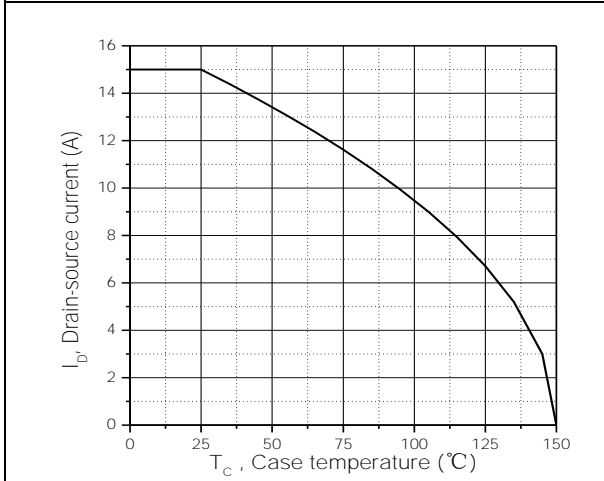


Figure 9. Drain current

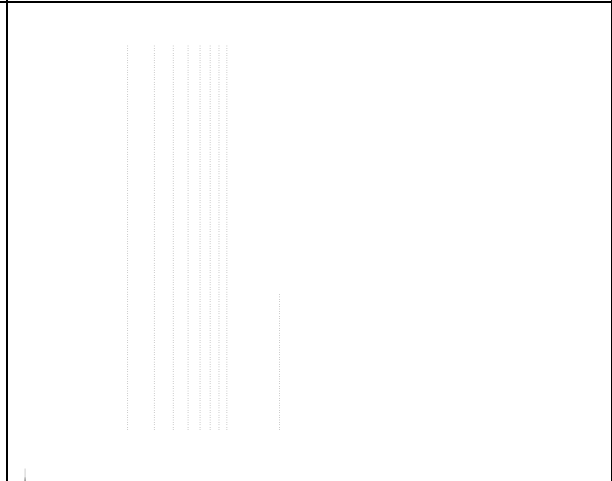


Figure 10. Safe operation area T_C=25

Test circuits and waveforms

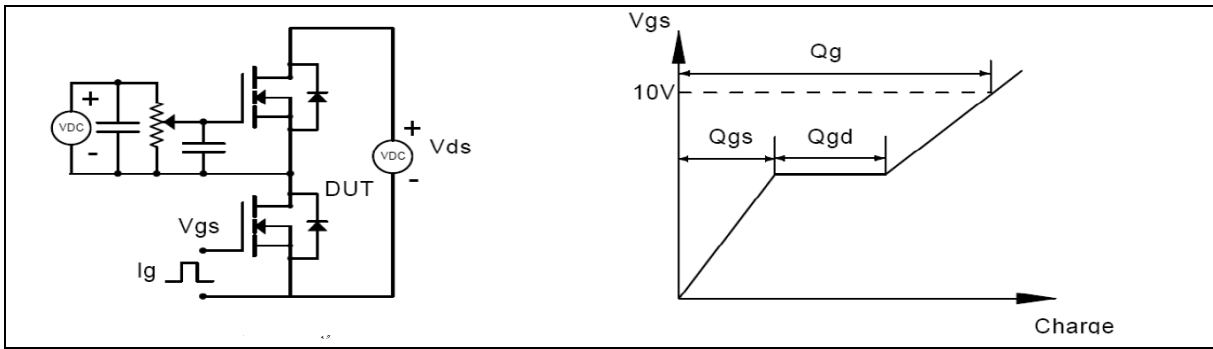


Figure 1. Gate charge test circuit & waveform

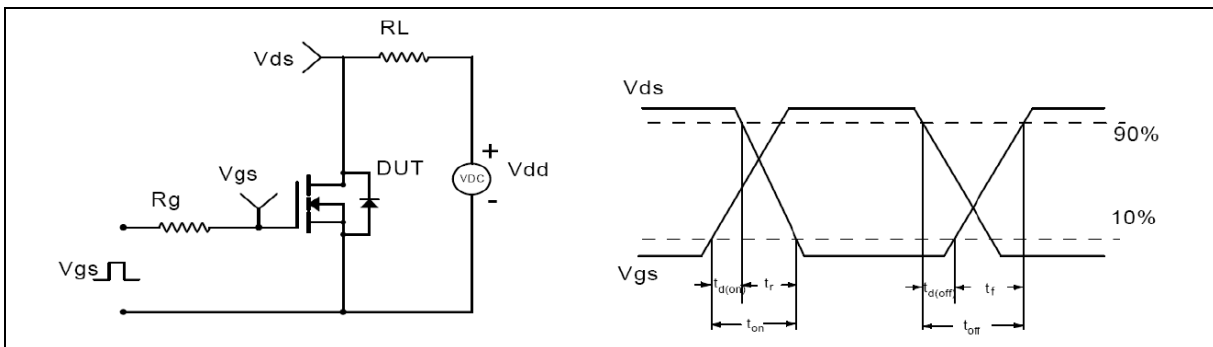


Figure 2. Switching time test circuit & waveforms

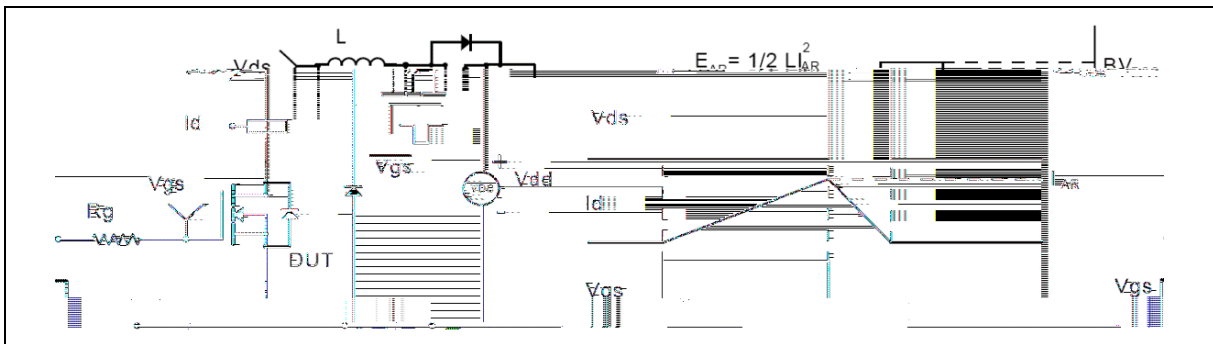


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

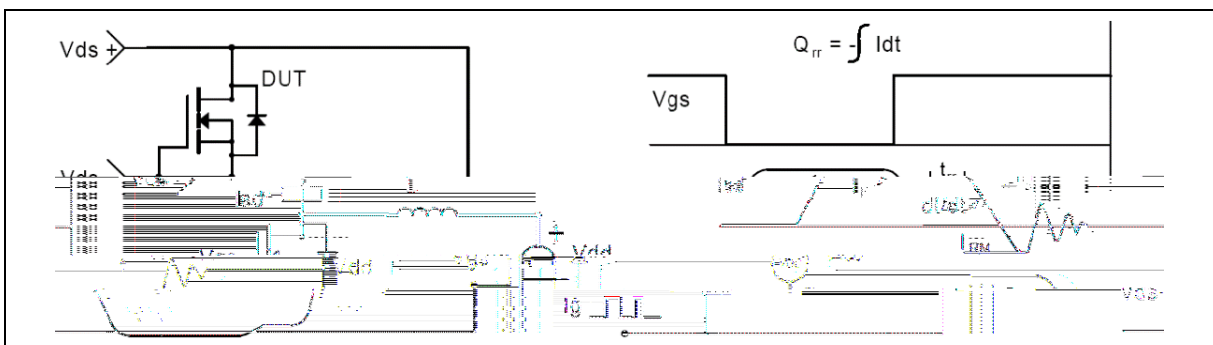
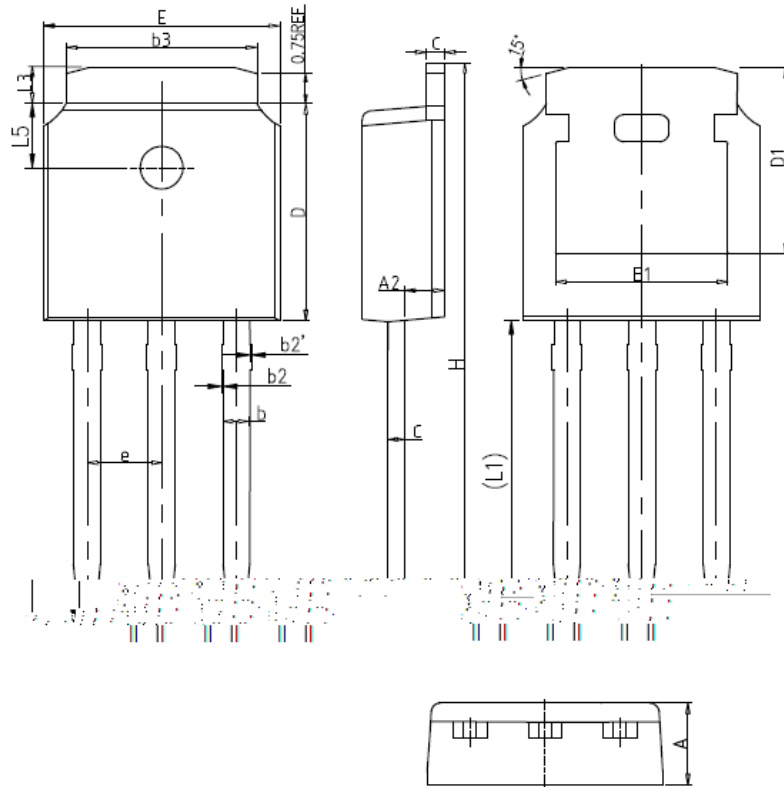


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	2.20	2.30	2.40
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b2	0.00	0.04	0.10
b2'	0.00	0.04	0.10
b3	5.20	5.33	5.50
c	0.43	0.53	0.63
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.80
E1	4.63	-	-
e	2.286BSC		
H	16.22	16.52	16.82
L1	9.15	9.40	9.65
L3	0.88	1.02	1.28
L5	1.65	1.80	1.95

Version1: TO251-C package outline dimension

